V_{RRM} = 1200 V
I_F = 75 A

Diode-Die

5SLX12F1200

Die size: 7.8 x 7.8 mm

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- **Fast Recovery, Low losses**
- **Soft reverse recovery**
- **High ruggedness**

Maximum Rated Values

(T_j = 25°C, unless specified otherwise)

Parameter	Symbol	Conditions	Values	Unit
Maximum Reverse Voltage	V_{RRM}		1200	V
DC Forward Current	I_F		75	A
Maximum Forward Current	I_{FM}	Limited by T_{jmax}	150	A
Operating Temperature	T_j		-40 .. +150	°C

Characteristic Values

(T_j = 25°C, unless specified otherwise)

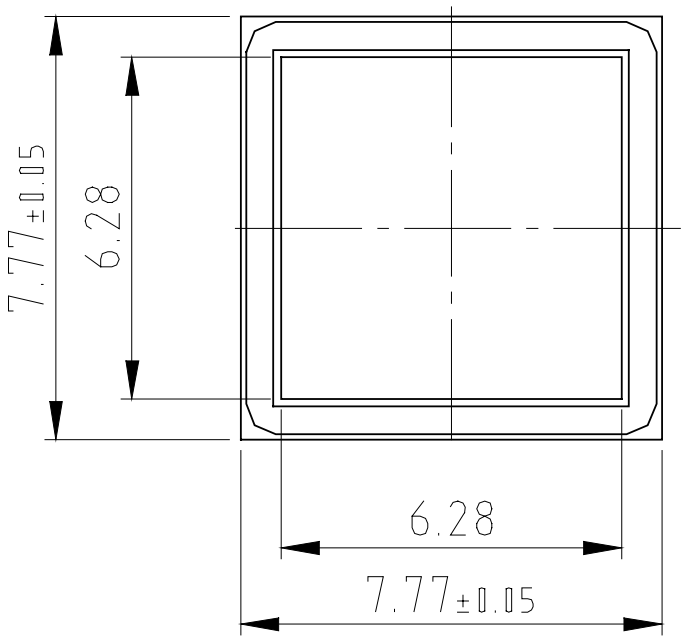
Parameter	Symbol	Conditions		min.	typ.	max.	Unit
Forward Voltage	V_F	I_F = 75 A	T_j = 25 °C	1.7	1.9	2.3	V
			T_j = 125 °C		1.9		V
Reverse leakage current	I_R	V_R = 1200 V	T_j = 25 °C			100	µA
			T_j = 125 °C		1		mA
Reverse recovery current	I_{rrm}	I_F = 75 A, V_{CC} = 600 V, di/dt = 1200 A/µs, L_σ = 50 nH, T_j = 125 °C, Inductive load, Switch : 5SMX12K1250			55		A
Reverse recovery charge	Q_{rr}				13		µC
Reverse recovery time	t_{rr}				400		ns
Reverse recovery energy	E_{rec}				4		mJ

Mechanical Characteristics

Parameter				Unit
Dimensions	Overall die	L x W	7.8 x 7.8	mm
	Exposed Front metal	L x W	6.2 x 6.2	mm
	Thickness		325 ± 15	µm
Metallization	Front	AlSi1	4.2	µm
	Back[1)]	Al / Ti / Ni / Ag	1.2	µm

[1)] For assembly instructions refer to : IGBT and Diode chips from ABB Switzerland Ltd, Semiconductors, Doc. No. 5SYA2033-01 April 02.

Outline Drawing



Note : All dimensions are shown in mm

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ABB Switzerland Ltd
Semiconductors
Fabrikstrasse 3
CH-5600 Lenzburg, Switzerland

Telephone +41 (0)58 586 1419
Fax +41 (0)58 586 1306
Email abbsem@ch.abb.com
Internet www.abbsem.com

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